

In the specification:

Please substitute the following paragraphs for the paragraphs at the indicated locations in the specification as originally filed or most recently amended.

Paragraph 0009:

In order to accomplish these and other objects of the invention, ~~A claim summary will be provided here when the claims are finalized~~ a mask structure and masking method are provided by depositing a material layer on a material surface which provides an interface selected from the group consisting of a chemical reaction interface, a grain interface and a material interface and provides increased resistance to semiconductor manufacturing processes and increased selectivity of an etching process to the material surface, lithographically patterning the material layer, and removing the material layer from the material surface selectively to the material surface.

Paragraph 0022:

The ability of converted TERA to be etched with HF in an organic or hygroscopic solvent derives principally from the conversion/hydration process described above in which OH⁻ groups are incorporated into the TERA material and provides water as a by-product of the etching process. This evolved water allows the local dissociation of HF to cause etching of the TERA film selectively to other films on the wafer since the evolved water will be rapidly bound by the organic or hygroscopic solvent which is preferably abundant in the mixture used for etching TERA as the evolved water diffuses into the etching mixture. (Statistically, a vanishingly small

amount of dissociation of HF will be present even when water is not present or otherwise bound by other materials such as an organic or hygroscopic solvent. Accordingly, a non-zero amount of etching activity of HF will ~~occurs~~ occur at the surface of the films (including TERA) on the wafer; allowing significant etching to proceed when water is evolved but effectively halting the etching process when water is not produced by the etching process or bound by the relative abundance of organic/hygroscopic material.) For example, ratios of 125:1 and 250:1 of ethylene glycol (a principal component of automotive anti-freeze) to HF has been found suitable for practice of the invention but such ratios should not be considered as limits for the process since the only necessary condition is that the organic or hygroscopic solvent be able to scavenge the amount of water which is evolved. This particular etching mixture is referred to as HF/EG. The temperature of the process is similarly non-critical and the selective TERA etching process has been successfully carried out over a temperature range of 65°C to 90°C with a preferred temperature of about 75°C but, again, these temperatures should not be considered as limits for the successful practice of the process.